PATENT
Docket No. 259052002900

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Tamara Alcaraz

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In the application of:

Masaaki KATOH

Serial No.: To Be Assigned

Filing Date: Herewith

For: LIGHT-EMITTING DIODE AND ITS MANUFACTURING METHOD

Examiner: To Be Assigned

Group Art Unit: To Be Assigned

PRELIMINARY AMENDMENT

Box: PATENT APPLICATION
Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

Prior to examination on the merits, applicant respectfully requests that the following amendment be entered.

pa-670132

AMENDMENTS

In the Specification:

On page 1, under BACKGROUND OF THE INVENTION, please insert the following paragraph:

--CROSS-REFERENCE TO RELATED APPLICATIONS

This application claims priority to Japanese Patent Application Number 2001-050558 filed February 26, 2001, and Japanese Patent Application Number 2002-41913 filed February 19, 2002, the contents of which are incorporated herein by reference in their entireties.--

In the Claims:

Please amend claims 4, 6, 8, and 10 as follows:

Please add new claims 12-27.

4. (Amended) A light-emitting diode claimed in Claim 1, wherein the light reflecting layer is formed of a metal thin film.

6. (Amended) A light-emitting diode claimed in Claim 4, wherein the metal thin film is formed of an Ni vapor-deposition film.

8. (Amended) A light-emitting diode claimed in Claim 1, wherein the Ni vapor-deposition film has a thickness of 100 nm or more.

10. (Amended) A light-emitting diode claimed in Claim 1, wherein the substrate is formed of a transparent substrate transparent to color emitted by the light-emitting diode chip.

Please add new claims 12-27

12. (New) A light-emitting diode claimed in Claim 2, wherein the light reflecting layer is formed of a metal thin film.

13. (New) A light-emitting diode claimed in Claim 5, wherein the metal thin film is formed of an Ni vapor-deposition film.

14. (New) A light-emitting diode claimed Claim 2, wherein the Ni vapor-deposition film has a thickness of 100 nm or more.

15. (New) A light-emitting diode claimed in Claim 3, wherein the Ni vapor-deposition film has a thickness of 100 nm or more.

16. (New) A light-emitting diode claimed in Claim 4, wherein the Ni vapor-deposition film has a thickness of 100 nm or more.

17. (New) A light-emitting diode claimed in Claim 5, wherein the Ni vapor-deposition film has a thickness of 100 nm or more.

18. (New) A light-emitting diode claimed in Claim 6, wherein the Ni vapor-deposition film has a thickness of 100 nm or more.

19. (New) A light-emitting diode claimed in Claim 7, wherein the Ni vapor-deposition film has a thickness of 100 nm or more.

20. (New) A light-emitting diode claimed in Claim 2, wherein the substrate is formed of a transparent substrate transparent to color emitted by the light-emitting diode chip.

21. (New) A light-emitting diode claimed in Claim 3, wherein the substrate is formed of a transparent substrate transparent to color emitted by the light-emitting diode chip.

22. (New) A light-emitting diode claimed in Claim 4, wherein the substrate is formed of a transparent substrate transparent to color emitted by the light-emitting diode chip.

23. (New) A light-emitting diode claimed in Claim 5, wherein the substrate is formed of a transparent substrate transparent to color emitted by the light-emitting diode chip.

24. (New) A light-emitting diode claimed in Claim 6, wherein the substrate is formed of a transparent substrate transparent to color emitted by the light-emitting diode chip.

25. (New) A light-emitting diode claimed in Claim 7, wherein the substrate is formed of a transparent substrate transparent to color emitted by the light-emitting diode chip.

26. (New) A light-emitting diode claimed in Claim 8, wherein the substrate is formed of a transparent substrate transparent to color emitted by the light-emitting diode chip.

27. (New) A light-emitting diode claimed in Claim 9, wherein the substrate is formed of a transparent substrate transparent to color emitted by the light-emitting diode chip.

REMARKS

Attached hereto is a marked-up version of the changes made to the specification and claims by the current amendment. The attached page is captioned "**Version with markings to show changes made**".

In the unlikely event that the transmittal letter is separated from this document and the Patent Office determines that an extension and/or other relief is required, applicant petitions for any required relief including extensions of time and authorizes the Assistant Commissioner to charge the cost of such petitions and/or other fees due in connection with the filing of this document to **Deposit Account No. 03-1952** referencing docket no. 259052002900.

Respectfully submitted,

Dated: February 26, 2002 By: _____

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VERSION WITH MARKINGS TO SHOW CHANGES MADE

In the Claims:

4. (Amended) A light-emitting diode claimed in Claim 1[or 2], wherein the light reflecting layer is formed of a metal thin film.

6. (Amended) A light-emitting diode claimed in Claim 4 [or 5], wherein the metal thin film is formed of an Ni vapor-deposition film.

8. (Amended) A light-emitting diode claimed in [any one of] Claim[s] 1[to 7], wherein the Ni vapor-deposition film has a thickness of 100 nm or more.

10. (Amended) A light-emitting diode claimed in Claim[s] 1[to 9], wherein the substrate is formed of a transparent substrate transparent to color emitted by the light-emitting diode chip.

Claims 12-27 have been added